

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
100V	5.0Ω@10V	0.2A
	5.5Ω@4.5V	

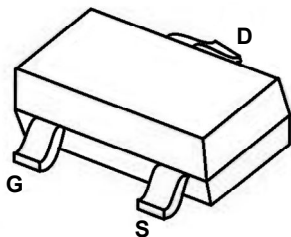
### Feature

- Voltage controlled small signal switch
- High density cell design for low  $R_{DS(ON)}$
- Fast Switching Speed

### Application

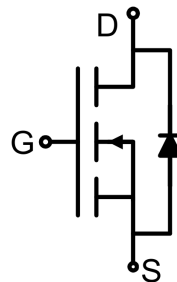
- Small servo motor control
- Power MOSFET gate drive
- Switching application

### Package

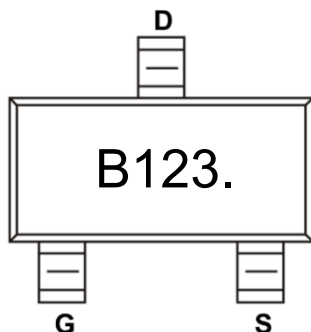


SOT-323

### Circuit diagram



### Marking



### Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current	$I_D$	0.2	A
Pulsed Drain Current	$I_{DM}$	0.8	A
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55 ~ +150	°C

### Electrical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 10\mu A$	100			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0		2.5	V
Drain-source on-resistance <sup>1)</sup>	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.2A$			5.0	Ω
		$V_{GS} = 4.5V, I_D = 0.2A$			5.5	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$		14		pF
Output Capacitance	$C_{oss}$			10		
Reverse Transfer Capacitance	$C_{rss}$			5		
Total Gate Charge	$Q_g$	$V_{DS} = 50V, V_{GS} = 10V, I_D = 0.2A$		1.8	2.5	nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50V, V_{GS} = 10V, I_D = 0.2A$ $R_{GEN} = 6\Omega$		1.7		nS
Turn-on rise time	$t_r$			9		
Turn-off delay time	$t_{d(off)}$			17		
Turn-off fall time	$t_f$			7		
<b>Source-Drain Diode characteristics</b>						
Diode Forward Current <sup>1)</sup>	$I_S$				0.2	A
Diode Forward voltage	$V_{DS}$	$V_{GS} = 0V, I_S = 0.2A$			1.2	V

Notes:

- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

## Typical Characteristics

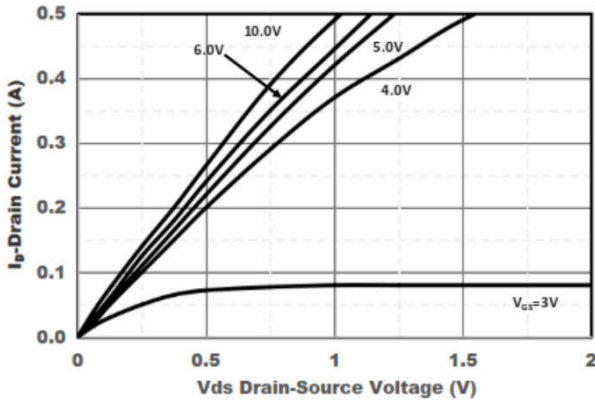


Figure1. Output Characteristics

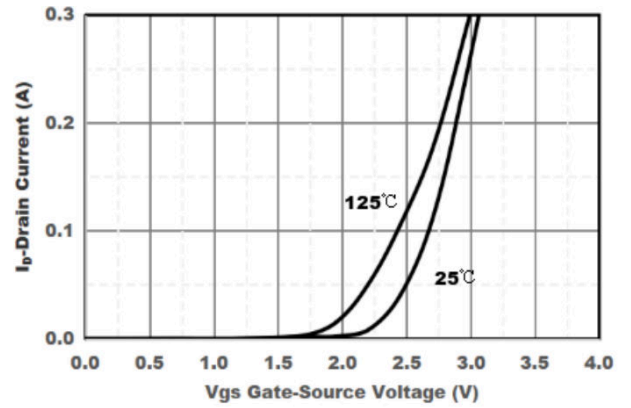


Figure2. Transfer Characteristics

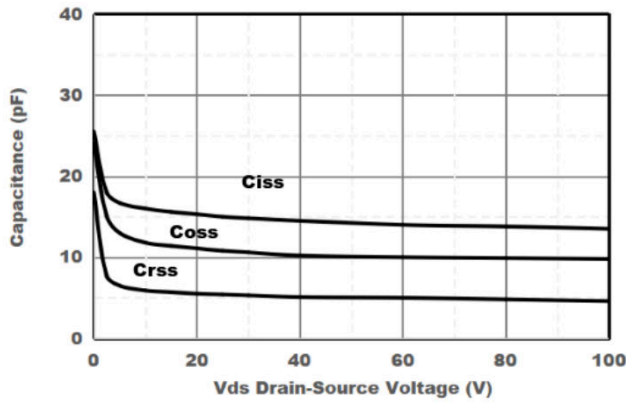


Figure3. Capacitance Characteristics

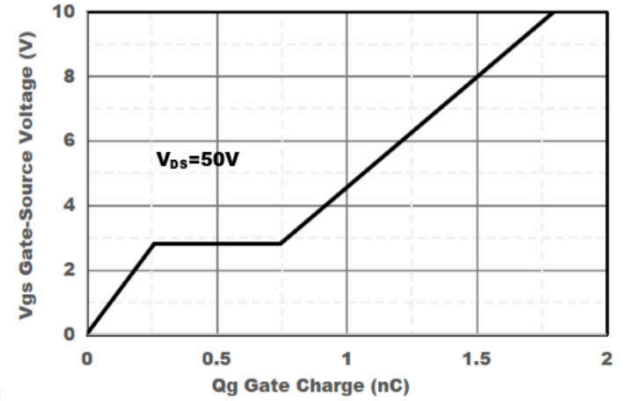


Figure4. Gate Charge

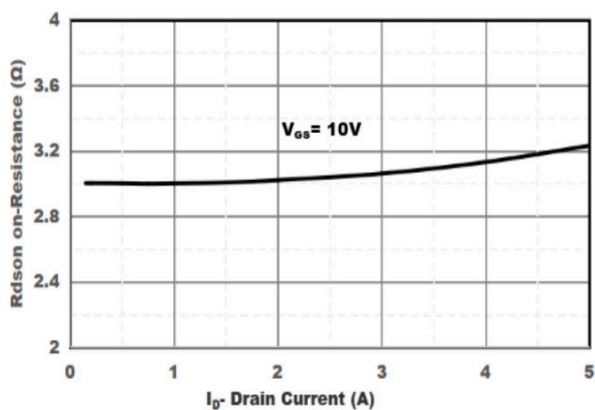


Figure5. Drain-Source on Resistance

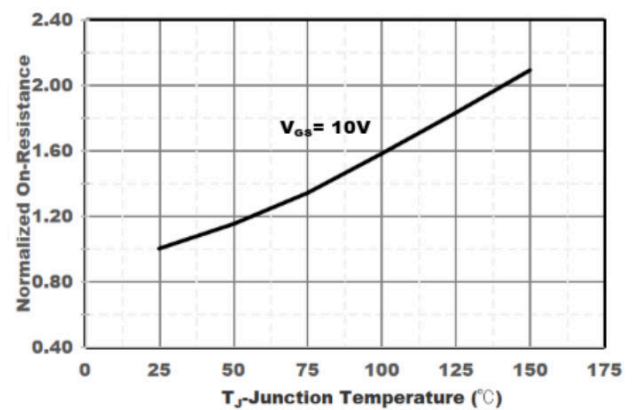
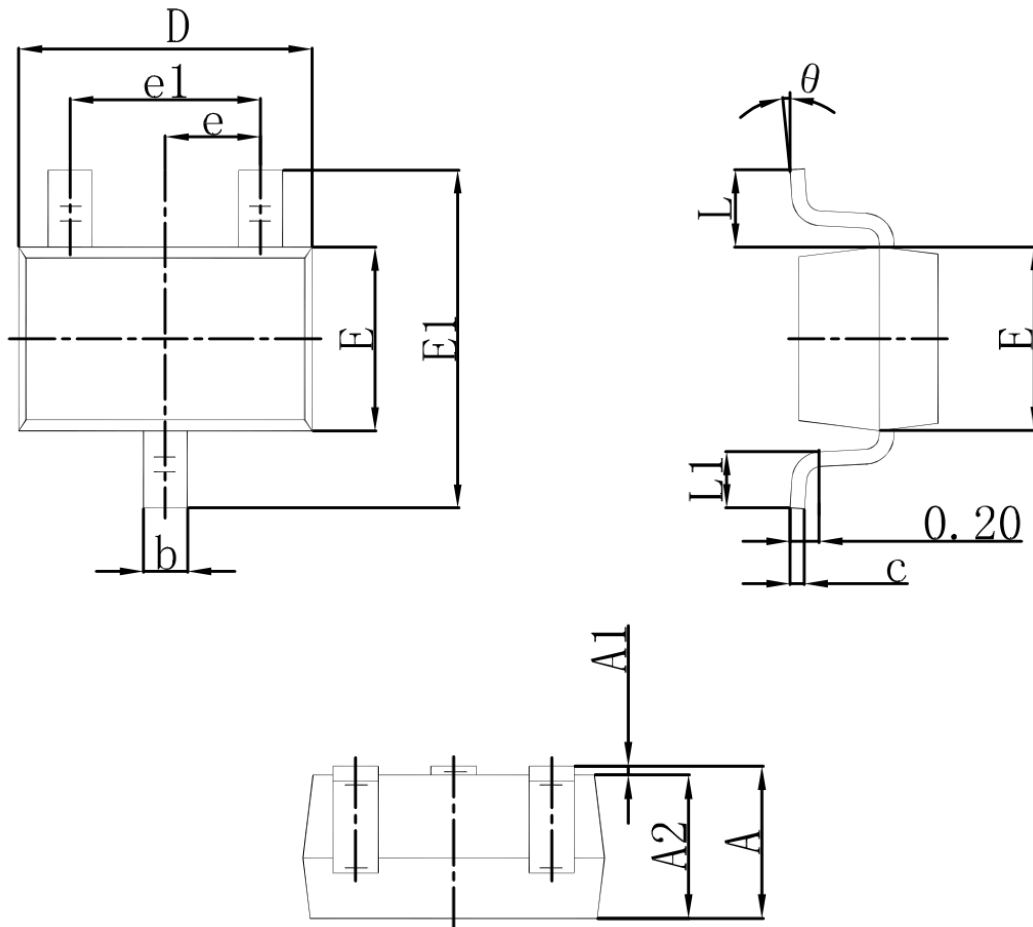


Figure6. Drain-Source on Resistance

### SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°